

74AHC1G06; 74AHCT1G06

Inverter with open-drain output

Rev. 06 — 7 June 2007

Product data sheet

1. General description

74AHC1G06 and 74AHCT1G06 are high-speed Si-gate CMOS devices. They provide an inverting buffer. The output of these devices is an open-drain and can be connected to other open-drain outputs to implement active-LOW, wired-OR or active-HIGH, wired-AND functions. For digital operation this device must have a pull-up resistor to establish a logic HIGH-level.

The AHC device has CMOS input switching levels and supply voltage range 2 V to 5.5 V.

The AHCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

2. Features

- High noise immunity
- Low power dissipation
- SOT353-1 and SOT753 package options
- ESD protection:
 - ◆ HBM JESD22-A114E: exceeds 2000 V
 - ◆ MM JESD22-A115-A: exceeds 200 V
 - ◆ CDM JESD22-C101C: exceeds 1000 V
- Specified from -40 °C to +125 °C

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC1G06GW 74AHCT1G06GW	-40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74AHC1G06GV 74AHCT1G06GV	-40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753

4. Marking

Table 2. Marking codes

Type number	Marking
74AHC1G06GW	AR
74AHC1G06GV	A06
74AHCT1G06GW	CR
74AHCT1G06GV	C06

5. Functional diagram

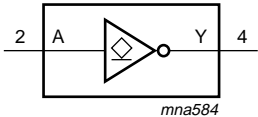


Fig 1. Logic symbol




Fig 2. IEC logic symbol

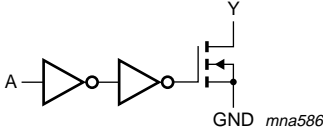


Fig 3. Logic diagram

6. Pinning information

6.1 Pinning

74AHC1G06
74AHCT1G06

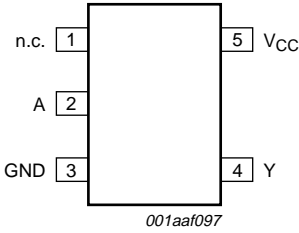


Fig 4. Pin configuration

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
n.c.	1	not connected
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state

Input	Output
A	Y
L	Z
H	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	-20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V	[1] -	±20	mA
I_O	output current	$V_O > -0.5$ V	-	±25	mA
V_O	output voltage	active mode	[1] -0.5	+7.0	V
		high-impedance mode	[1] -0.5	+7.0	V
I_{CC}	supply current		-	75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For both TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74AHC1G06			74AHCT1G06			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	0	-	5.5	V
V_O	output voltage	active mode	0	-	V_{CC}	0	-	V_{CC}	V
		high-impedance mode	0	-	6.0	0	-	6.0	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.3$ V ± 0.3 V	-	-	100	-	-	-	ns/V
		$V_{CC} = 5.0$ V ± 0.5 V	-	-	20	-	-	20	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
For type 74AHC1G06										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.25		±2.5		±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	20	μA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF
For type 74AHCT1G06										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.25		±2.5		±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.0	-	10	-	20	μA
ΔI _{CC}	additional supply current	per input pin; V _I = 3.4 V; other inputs at V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance		-	1.5	10	-	10	-	10	pF

11. Dynamic characteristics

Table 8. Dynamic characteristics

$GND = 0\text{ V}$; $t_r = t_f \leq 3.0\text{ ns}$. For test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	

For type 74AHC1G06

t _{PZL}	OFF-state to LOW propagation delay	A to Y; see Figure 5								
		V _{CC} = 3.0 V to 3.6 V [1]								
		C _L = 15 pF	-	3.7	7.0	1.0	7.7	1.0	8.1	ns
		C _L = 50 pF	-	5.2	10.0	1.0	11.0	1.0	11.5	ns
		V _{CC} = 4.5 V to 5.5 V [2]								
		C _L = 15 pF	-	2.7	4.9	1.0	5.3	1.0	5.6	ns
t _{PLZ}	LOW to OFF-state propagation delay	A to Y; see Figure 5								
		V _{CC} = 3.0 V to 3.6 V [1]								
		C _L = 15 pF	-	4.8	6.4	1.0	6.9	1.0	7.4	ns
		C _L = 50 pF	-	6.9	10.0	1.0	10.5	1.0	11.0	ns
		V _{CC} = 4.5 V to 5.5 V [2]								
		C _L = 15 pF	-	3.0	4.1	1.0	4.6	1.0	5.1	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	-	3	-	-	-	-	-	pF

For type 74AHCT1G06

t _{PZL}	OFF-state to LOW propagation delay	A to Y; see Figure 5								
		V _{CC} = 4.5 V to 5.5 V [2]								
		C _L = 15 pF	-	3.0	5.3	1.0	6.0	1.0	6.3	ns
t _{PLZ}	LOW to OFF-state propagation delay	A to Y; see Figure 5								
		V _{CC} = 4.5 V to 5.5 V [2]								
		C _L = 15 pF	-	3.2	4.6	1.0	5.1	1.0	5.6	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF	-	4.5	7.0	1.0	7.5	1.0	8.0	ns
		per buffer; C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC}	-	4.5	-	-	-	-	-	pF

[1] Typical values are measured at V_{CC} = 3.3 V.

[2] Typical values are measured at V_{CC} = 5.0 V.

[3] C_{PD} is used to determine the dynamic power dissipation P_D (μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts

12. Waveforms

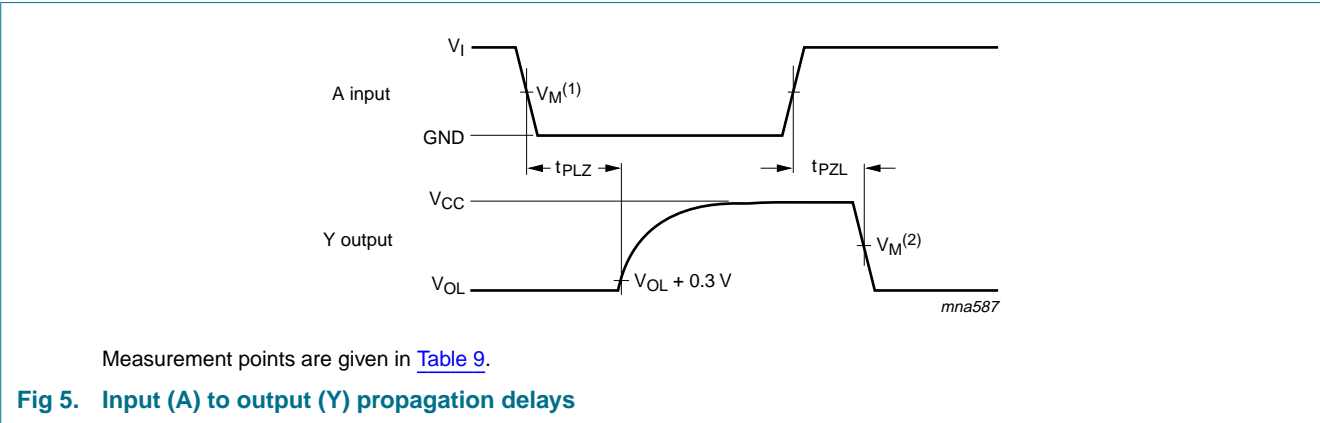
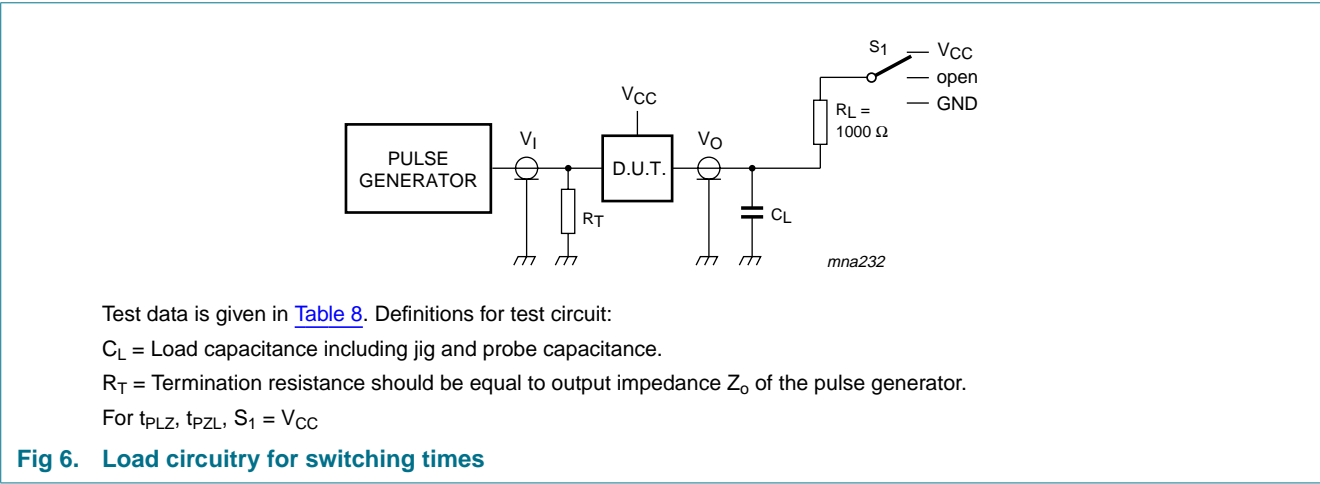


Table 9. Measurement point

Type	Input		Output
	V _I	V _M ⁽¹⁾	V _M ⁽²⁾
74AHC1G06	GND to V _{CC}	0.5 × V _{CC}	0.5 × V _{CC}
74AHCT1G06	GND to 3.0 V	1.5 V	0.5 × V _{CC}



13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mmSOT353-1

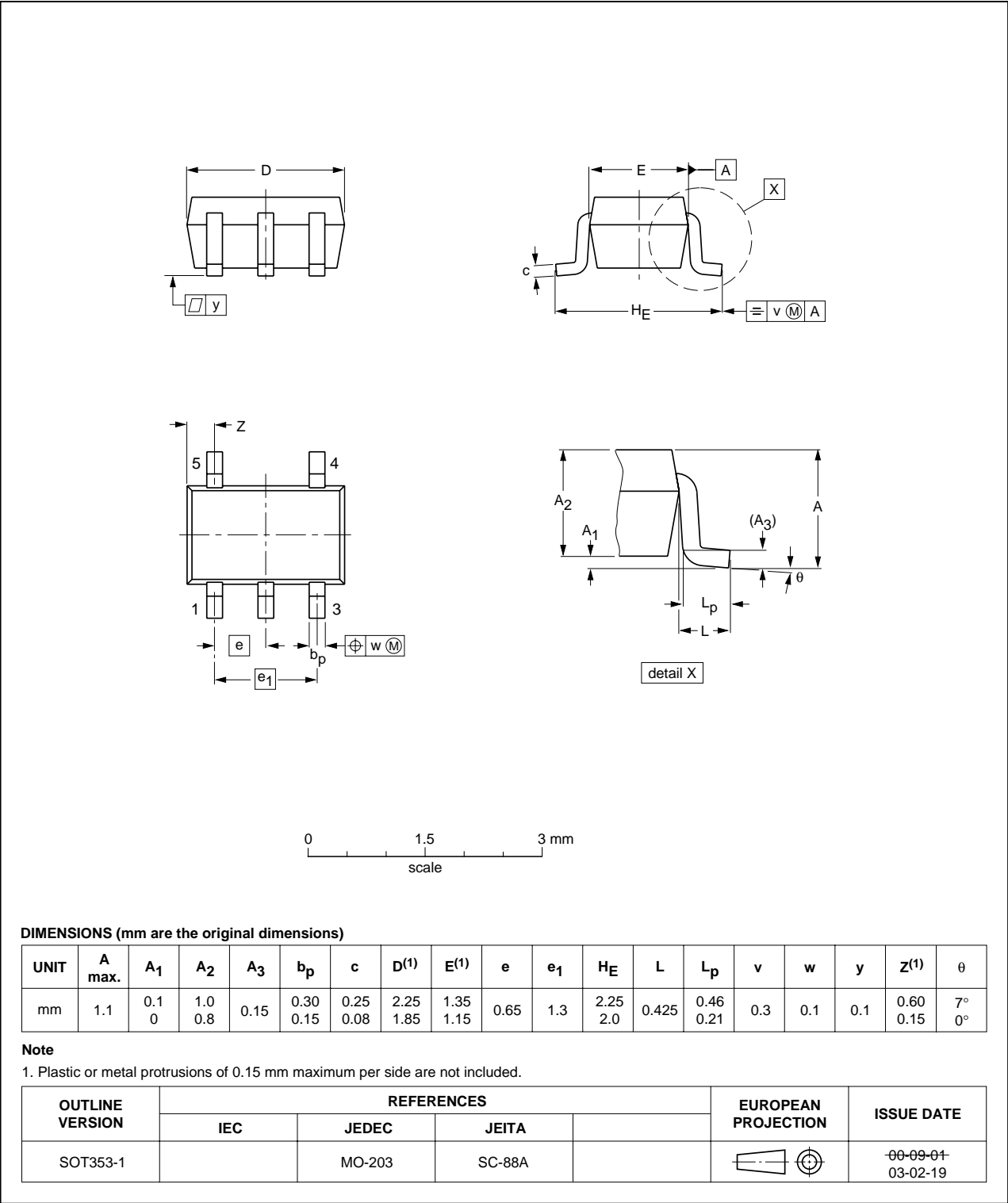


Fig 7. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

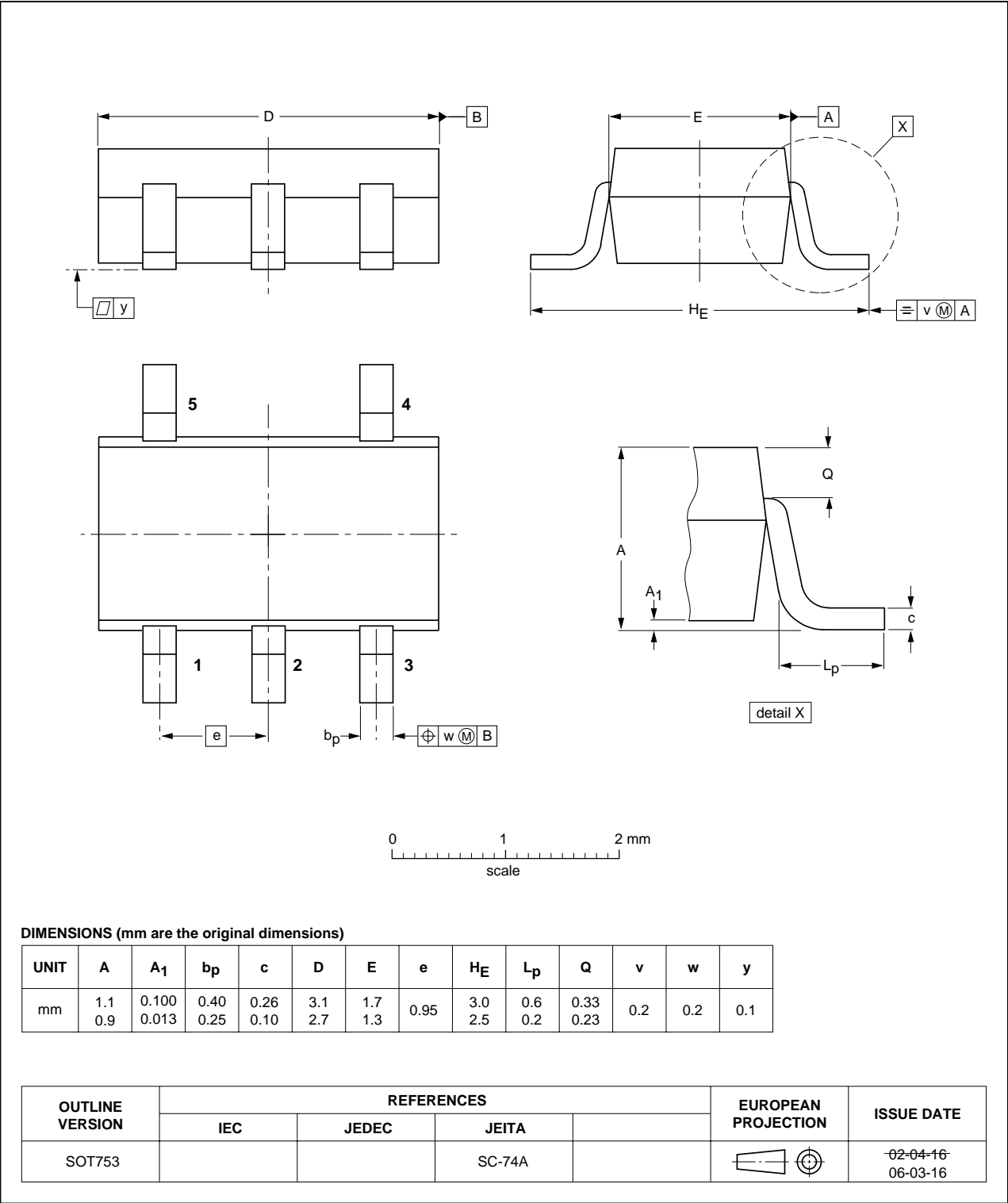


Fig 8. Package outline SOT753 (SC-74A)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT1G06_6	20070607	Product data sheet	-	74AHC_AHCT1G06_5
Modifications:	<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Package SOT353 changed to SOT353-1 in Section 3 and Section 13.• Quick reference data and Soldering sections removed.			
74AHC_AHCT1G06_5	20021002	Product specification	-	74AHC_AHCT1G06_4
74AHC_AHCT1G06_4	20020528	Product specification	-	74AHC_AHCT1G06_3
74AHC_AHCT1G06_3	20020221	Product specification	-	74AHC_AHCT1G06_2
74AHC_AHCT1G06_2	20010209	Product specification	-	74AHC_AHCT1G06_1
74AHC_AHCT1G06_1	20000501	Product specification	-	-

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16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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18. Contents

1	General description	1
2	Features	1
3	Ordering information	1
4	Marking	2
5	Functional diagram	2
6	Pinning information	2
6.1	Pinning	2
6.2	Pin description	2
7	Functional description	3
8	Limiting values	3
9	Recommended operating conditions	3
10	Static characteristics	4
11	Dynamic characteristics	5
12	Waveforms	6
13	Package outline	7
14	Abbreviations	9
15	Revision history	9
16	Legal information	10
16.1	Data sheet status	10
16.2	Definitions	10
16.3	Disclaimers	10
16.4	Trademarks	10
17	Contact information	10
18	Contents	11

